Low Noise Transistor

PNP Silicon

Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	-50	Vdc
Collector-Base Voltage	V _{CBO}	-50	Vdc
Emitter-Base Voltage	V _{EBO}	-3.0	Vdc
Collector Current – Continuous	Ι _C	-50	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board, (Note 1) T _A = 25°C Derate above 25°C	PD	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R_{\thetaJA}	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

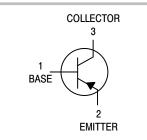
1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.



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SOT-23 (TO-236) **CASE 318 STYLE 6**

MARKING DIAGRAM



2Q = Device Code M = Date Code*

• = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

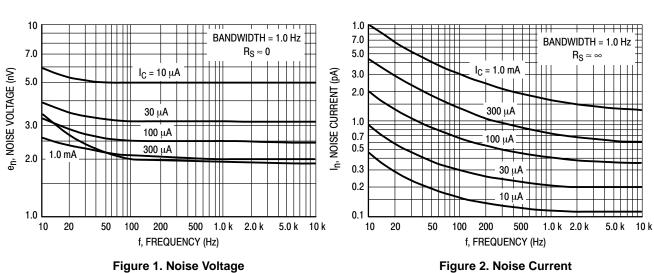
Device	Package	Shipping [†]
MMBT5087LT1G,	SOT–23	3,000 / Tape &
NSVMMBT5087LT1G	(Pb–Free)	Reel
MMBT5087LT3G,	SOT-23	10,000 / Tape &
NSVMMBT5087LT3G	(Pb-Free)	Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Мах	Unit
OFF CHARACTERISTICS		•		
Collector–Emitter Breakdown Voltage ($I_C = -1.0 \text{ mAdc}, I_B = 0$)	V _{(BR)CEO}	-50	_	Vdc
Collector–Base Breakdown Voltage ($I_C = -100 \ \mu Adc, I_E = 0$)	V _{(BR)CBO}	-50	-	Vdc
Collector Cutoff Current $(V_{CB} = -10 \text{ Vdc}, I_E = 0)$ $(V_{CB} = -35 \text{ Vdc}, I_E = 0)$	I _{CBO}		-10 -50	nAdc
ON CHARACTERISTICS	·			•
DC Current Gain $(I_C = -100 \ \mu Adc, \ V_{CE} = -5.0 \ Vdc)$ $(I_C = -1.0 \ m Adc, \ V_{CE} = -5.0 \ Vdc)$ $(I_C = -10 \ m Adc, \ V_{CE} = -5.0 \ Vdc)$	h _{FE}	250 250 250	800 - -	-
Collector–Emitter Saturation Voltage ($I_c = -10$ mAdc, $I_B = -1.0$ mAdc)	V _{CE(sat)}	-	-0.3	Vdc
Base–Emitter Saturation Voltage ($I_c = -10 \text{ mAdc}, I_B = -1.0 \text{ mAdc}$)	V _{BE(sat)}	-	0.85	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current–Gain — Bandwidth Product ($I_C = -500 \ \mu Adc$, $V_{CE} = -5.0 \ Vdc$, f = 20 MHz)	f _T	40	_	MHz
Output Capacitance ($V_{CB} = -5.0 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz}$)	C _{obo}	-	4.0	pF
Small–Signal Current Gain (I _C = –1.0 mAdc, V _{CE} = –5.0 Vdc, f = 1.0 kHz)	h _{fe}	250	900	-
Noise Figure ($I_C = -20 \text{ mAdc}$, $V_{CE} = -5.0 \text{ Vdc}$, $R_S = 10 \text{ k}\Omega$, f = 1.0 kHz) ($I_C = -100 \mu \text{Adc}$, $V_{CE} = -5.0 \text{ Vdc}$, $R_S = 3.0 \text{ k}\Omega$, f = 1.0 kHz)	NF		2.0 2.0	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



TYPICAL NOISE CHARACTERISTICS

 $(V_{CE}=-5.0 \text{ Vdc}, \text{ } \text{T}_{\text{A}}=25^{\circ}\text{C})$

NOISE FIGURE CONTOURS

 $(V_{CE} = -5.0 \text{ Vdc}, T_A = 25^{\circ}C)$

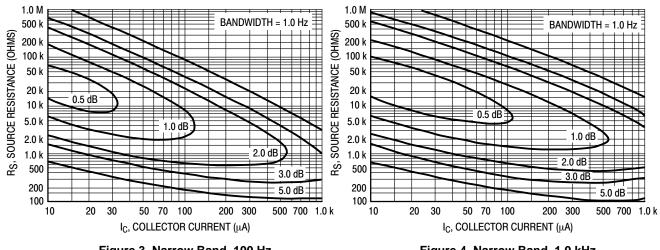
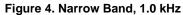


Figure 3. Narrow Band, 100 Hz



Noise Figure is Defined as:

$$NF = 20 \log_{10} \left[\frac{e_{n}^{2} + 4KTR_{S} + I_{n}^{2}R_{S}^{2}}{4KTR_{S}} \right]^{1/2}$$

e_n = Noise Voltage of the Transistor referred to the input. (Figure 3)

= Noise Current of the Transistor referred to the input. (Figure 4) I_{n}

K = Boltzman's Constant (1.38 x 10⁻²³ j/°K)

T = Temperature of the Source Resistance (°K)

R_S = Source Resistance (Ohms)

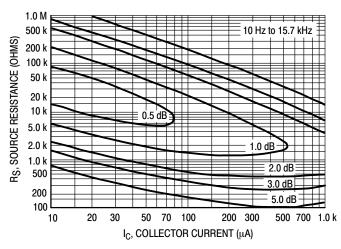


Figure 5. Wideband

TYPICAL STATIC CHARACTERISTICS

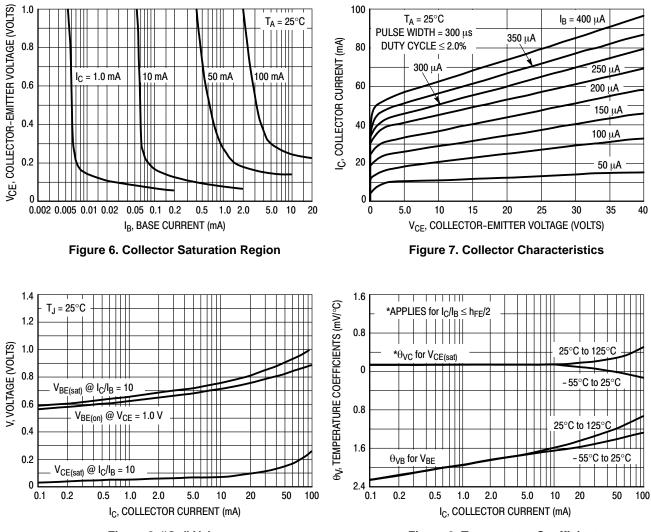


Figure 8. "On" Voltages

Figure 9. Temperature Coefficients

TYPICAL DYNAMIC CHARACTERISTICS

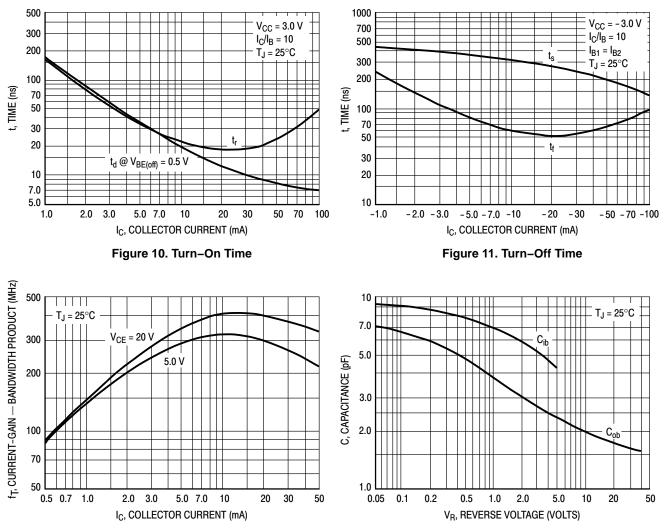


Figure 12. Current–Gain — Bandwidth Product

Figure 13. Capacitance

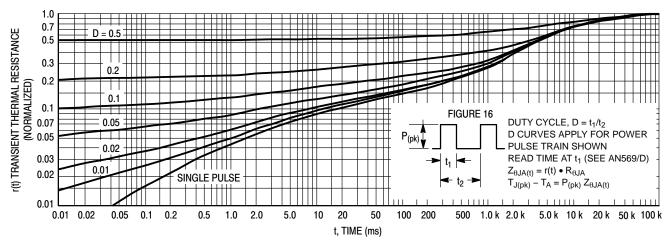


Figure 14. Thermal Response

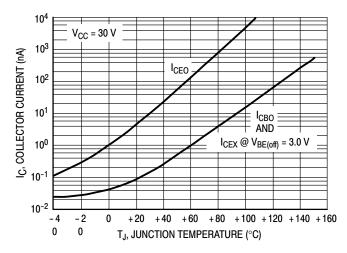


Figure 15. Typical Collector Leakage Current

DESIGN NOTE: USE OF THERMAL RESPONSE DATA

A train of periodical power pulses can be represented by the model as shown in Figure 16. Using the model and the device thermal response the normalized effective transient thermal resistance of Figure 14 was calculated for various duty cycles.

To find $Z_{\theta JA(t)}$, multiply the value obtained from Figure 14 by the steady state value $R_{\theta JA}$.

Example:

Dissipating 2.0 watts peak under the following conditions: $t_1 = 1.0 \text{ ms}, t_2 = 5.0 \text{ ms} (D = 0.2)$

Using Figure 14 at a pulse width of 1.0 ms and D = 0.2, the reading of r(t) is 0.22.

The peak rise in junction temperature is therefore

 $\Delta T = r(t) \ge P_{(pk)} \ge R_{\theta JA} = 0.22 \ge 2.0 \ge 200 = 88^{\circ}C.$

For more information, see ON Semiconductor Application Note AN569/D, available from the Literature Distribution Center or on our website at **www.onsemi.com**.

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

D

3

TOP VIEW

SIDE VIEW

Нe

DETAIL A

-3X b

DUSem



SCALE 4:1

Α A1SOT-23 (TO-236) **CASE 318 ISSUE AT**

0.25

-L1

DETAIL A

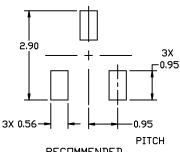
END VIEW

DATE 01 MAR 2023

NDTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- CONTROLLING DIMENSION: MILLIMETERS 2.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS DF THE BASE MATERIAL. З.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. 4.

	MILLIMETERS			INCHES		
DIM	MIN.	NDM.	MAX.	MIN.	NDM.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
с	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
Η _E	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10*	0*		10*



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D. *

GENERIC **MARKING DIAGRAM***



XXX = Specific Device Code

М = Date Code

= Pb-Free Package .

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

onsemi

SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE	2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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